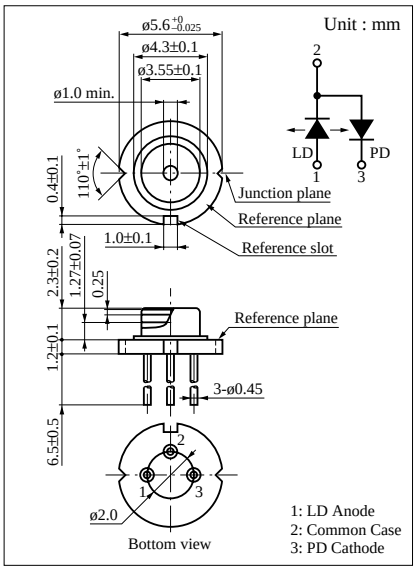
LNC702PS

GaAlAs Semiconductor Laser



Features

- Low threshold current
- Stable single horizontal mode oscillation
- Low drooping

Applications

- Optical data processing devices
- Laser beam printers

Absolute Maximum Ratings (Ta = 25˚C)

Parameter		Symbol	Ratings	Unit
Radiant power		P_O	5	mW
Reverse voltage	Laser	V_R	2	V
	PIN	V_R (PIN)	30	V
Power dissipation		P_d (PIN)	60	mW
Operating ambient temperature		T_{opr}	–10 to +60	˚C
Storage temperature		T_{stg}	– 40 to +85	˚C

Electro-Optical Characteristics (Ta = 25˚C)

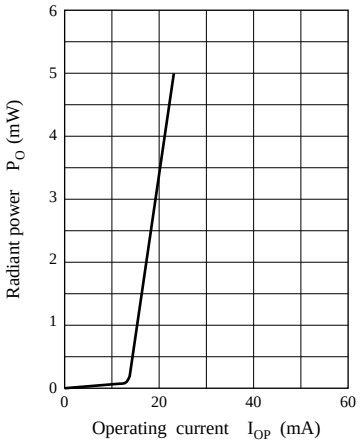
Parameter		Symbol	Conditions	min	typ	max	Unit
Threshold current		I_{th}	CW	15	25	40	mA
Operating current		I_{OP}	CW P_O = 5mW	20	35	50	mA
Operating voltage		V_{OP}	CW P_O = 5mW		1.9	2.5	V
Oscillation wavelength		λ_L *2	CW P_O = 5mW	780	795	810	nm
Radiation angle	Horizontal direction	$\theta_{//}$ *1	CW P_O = 5mW	8	12	15	deg.
	Vertical direction	$\theta_{\perp}$ *1	CW P_O = 5mW	20	33	45	deg.
PIN photo current		I_P	CW P_O = 5mW, V_R (PIN) = 5V	0.3	0.8	1.6	mA
Reverse current (DC)		I_R	V_R (PIN) = 15V			0.1	µA
Optical axis accuracy	X direction	θ_X	CW P_O = 5mW	–2.0		+2.0	deg.
	Y direction	θ_Y	CW P_O = 5mW	–3.0		+3.0	deg.

*1 The radiation angle is indicated as half full angle.

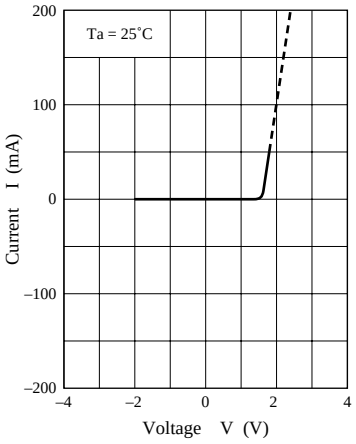
*2 Sampling inspections are to be performed.

On each wafer, n = 10 samplings are to be performed, with an evaluation criterion of zero rejects.

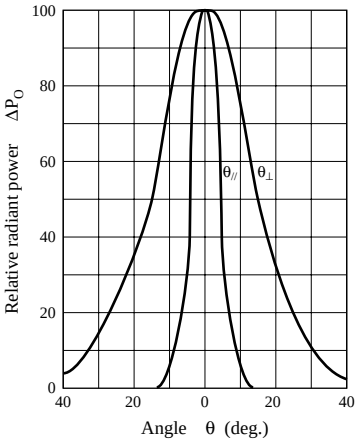
P_O — I_{OP}



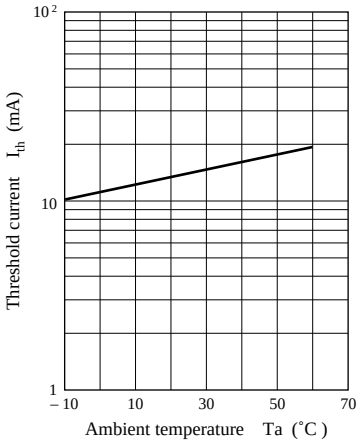
I — V



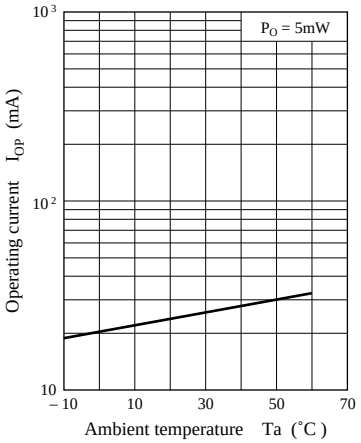
Far field pattern



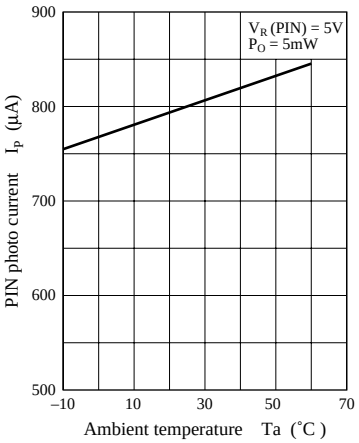
I_{th} — Ta



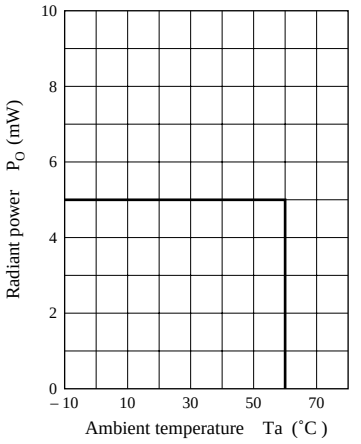
I_{OP} — Ta



I_P — Ta



P_O — Ta



I_d — Ta